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Question Paper Code: 21469

B.E./B.Tech. DEGREE EXAMINATION, NOVEMBER/DECEMBER 2015.

Seventh Semester

Electronics and Communication Engineering

EC 2403/EC 73/10144 EC 703 — RF AND MICROWAVE ENGINEERING

(Regulations 2008/2010)

(Common to PTEC 2403 – RF and Microwave Engineering for B.E. (Part-Time) Sixth Semester Electronics and Communication Engineering – Regulations 2009)

Time: Three hours

Maximum: 100 marks

Smith Chart is to be provided.

Answer ALL questions.

$$PART A - (10 \times 2 = 20 \text{ marks})$$

1. Find the 'S' parameters for the following network.

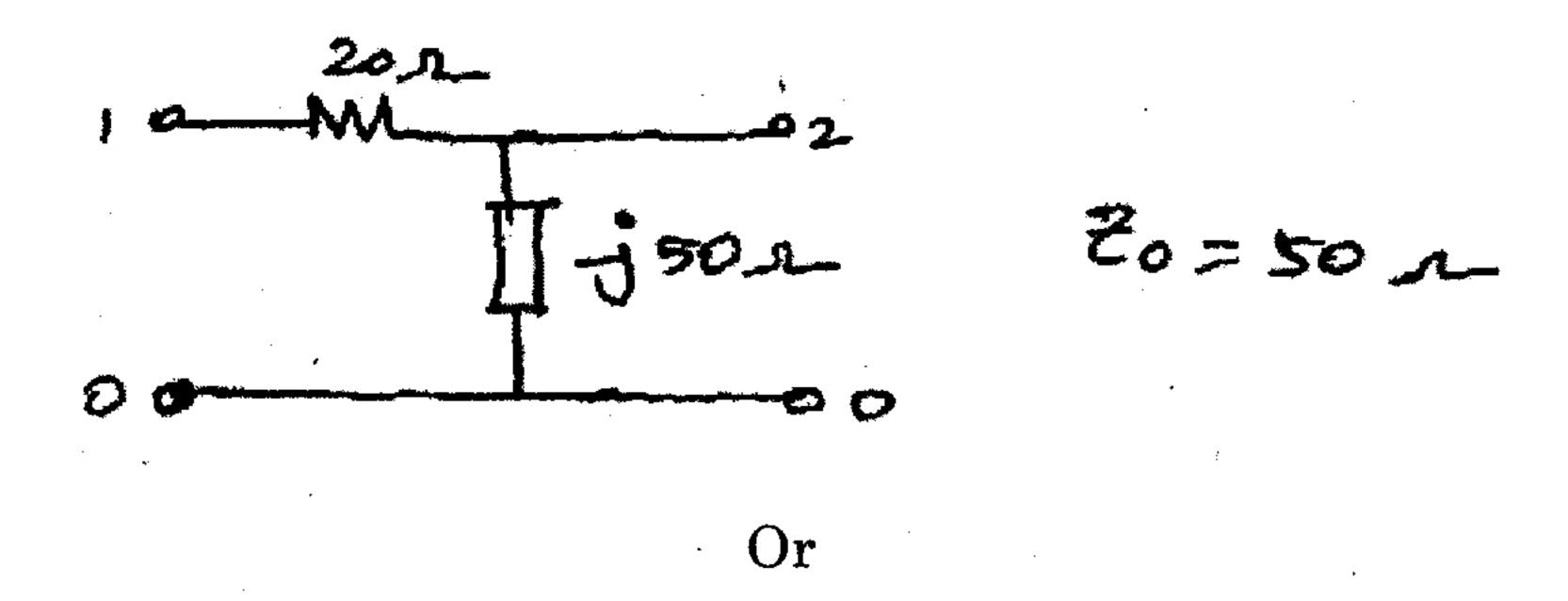
$$1002$$
 1752
 $20 = 752$

- 2. Identify the type of component with S parameters of $S_{11} = S_{12} = 0$, $S_{21} \neq S_{22}$.
- 3. Define maximum available gain.
- 4. What are the advantages of microstrip line matching networks?
- 5. What are the applications of Magic Tee?
- 6. What are the S parameters of the rotary type attenuator with rotation angle of 30°?
- 7. What is the working principle of varactor diode?
- 8. State Gunn effect.

- 9. What are the limitations of conventional tubes at microwave frequency?
- 10. What are the methods used to measure the attenuation at microwave frequency?

PART B —
$$(5 \times 16 = 80 \text{ marks})$$

- 11. (a) (i) State and verify the symmetry property of the reciprocal networks. (8)
 - (ii) Find the S parameters for the following circuit. (8)



- (b) (i) Draw the high frequency equivalent of wire, resistor, inductor and capacitor and explain. (8)
 - (ii) Evaluate the S parameters from the Z parameters. (8)

$$[Z] = \begin{bmatrix} 2+3j & 5j \\ 3j & -j \end{bmatrix}, Z_0 = 50\Omega.$$

- 12. (a) Design all the possible configurations of discrete two element matching network that match the source impedance $Z_S = (50 + j 25)\Omega$ to the load $Z_L = (25 j15)\Omega$. Assume the characteristic impedance of 75 Ω at operating frequency 2 GHz. (16)
 - (b) Draw the 8 dB gain circle of the transistor with following S parameters at 1 GHz. $S_{11} = 0.46 < -97^{\circ}$, $S_{12} = 0.06 < -22^{\circ}$, $S_{21} = 7.1 < 112^{\circ}$ and $S_{22} = 0.57 < -48^{\circ}$. (16)
- 13. (a) (i) Explain the working principle of E plane Tee and derive its S parameters. (8)
 - (ii) Explain the working of phase shifter with neat diagram. (8)
 Or
 - (b) (i) Explain the working of circulator and explain its applications. (10)
 - (ii) Explain the working principle of isolator. (6)

14. (a) Explain the working principle of Gunn diode oscillator and its modes. (16)

Or

- (b) Explain the working principle of IMPATT diode with neat diagram. (16)
- 15. (a) Explain the working principle of Travelling Wave Tube Amplifier (TWTA). (16)

Or

(b) Explain the working principle of reflex klystron oscillator and derive the expression for power and efficiency. (16)